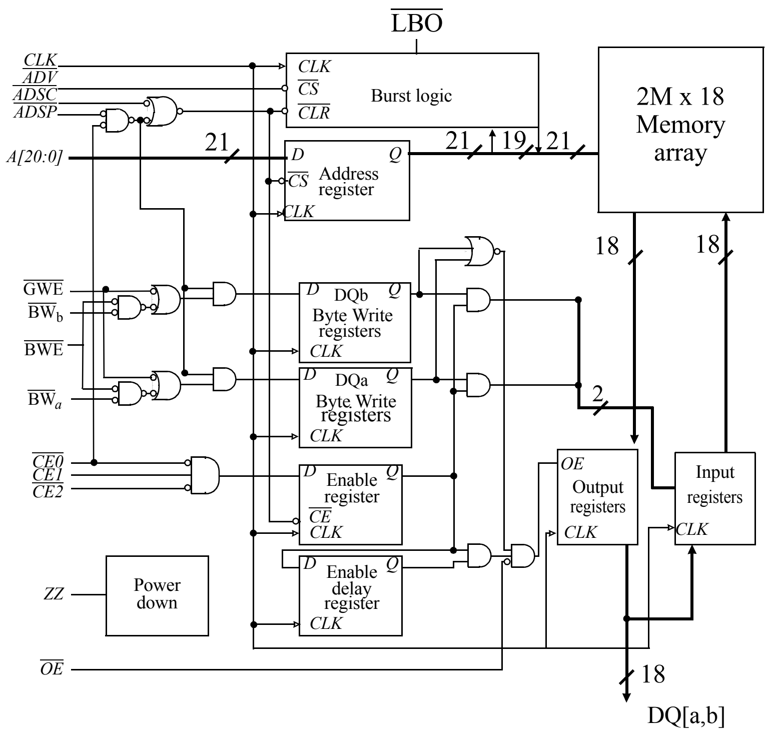
3.3V 2M × 18 Flow-through synchronous SRAM

Features

- Organization: 2,097152 words × 18 bits
- Fast clock to data access: 7.5/8.5/10 ns
- Fast $\overline{OE}$ access time: 3.5/4.0 ns
- Fully synchronous flow-through operation
- Asynchronous output enable control
- Available in 100-pin TQFP package
- Individual byte write and global write
- Multiple chip enables for easy expansion
- 3.3V core power supply
- 2.5V or 3.3V I/O operation with separate V_{DDQ}
- Linear or interleaved burst control
- Snooze mode for reduced power-standby
- Common data inputs and data outputs

Logic block diagram



Selection guide

	-75	-85	-10	Units
Minimum cycle time	8.5	10	12	ns
Maximum clock access time	7.5	8.5	10	ns
Maximum operating current	325	300	275	mA
Maximum standby current	140	130	130	mA
Maximum CMOS standby current (DC)	90	90	90	mA

32 Mb Synchronous SRAM products list[1,2]

Org	Part Number	Mode	Speed
2MX18	AS7C332MPFS18A	PL-SCD	200/166/133 MHz
1MX32	AS7C331MPFS32A	PL-SCD	200/166/133 MHz
1MX36	AS7C331MPFS36A	PL-SCD	200/166/133 MHz
2MX18	AS7C332MPFD18A	PL-DCD	200/166/133 MHz
1MX32	AS7C331MPFD32A	PL-DCD	200/166/133 MHz
1MX36	AS7C331MPFD36A	PL-DCD	200/166/133 MHz
2MX18	AS7C332MFT18A	FT	7.5/8.5/10 ns
1MX32	AS7C331MFT32A	FT	7.5/8.5/10 ns
1MX36	AS7C331MFT36A	FT	7.5/8.5/10 ns
2MX18	AS7C332MNTD18A	NTD-PL	200/166/133 MHz
1MX32	AS7C331MNTD32A	NTD-PL	200/166/133 MHz
1MX36	AS7C331MNTD36A	NTD-PL	200/166/133 MHz
2MX18	AS7C332MNTF18A	NTD-FT	7.5/8.5/10 ns
1MX32	AS7C331MNTF32A	NTD-FT	7.5/8.5/10 ns
1MX36	AS7C331MNTF36A	NTD-FT	7.5/8.5/10 ns

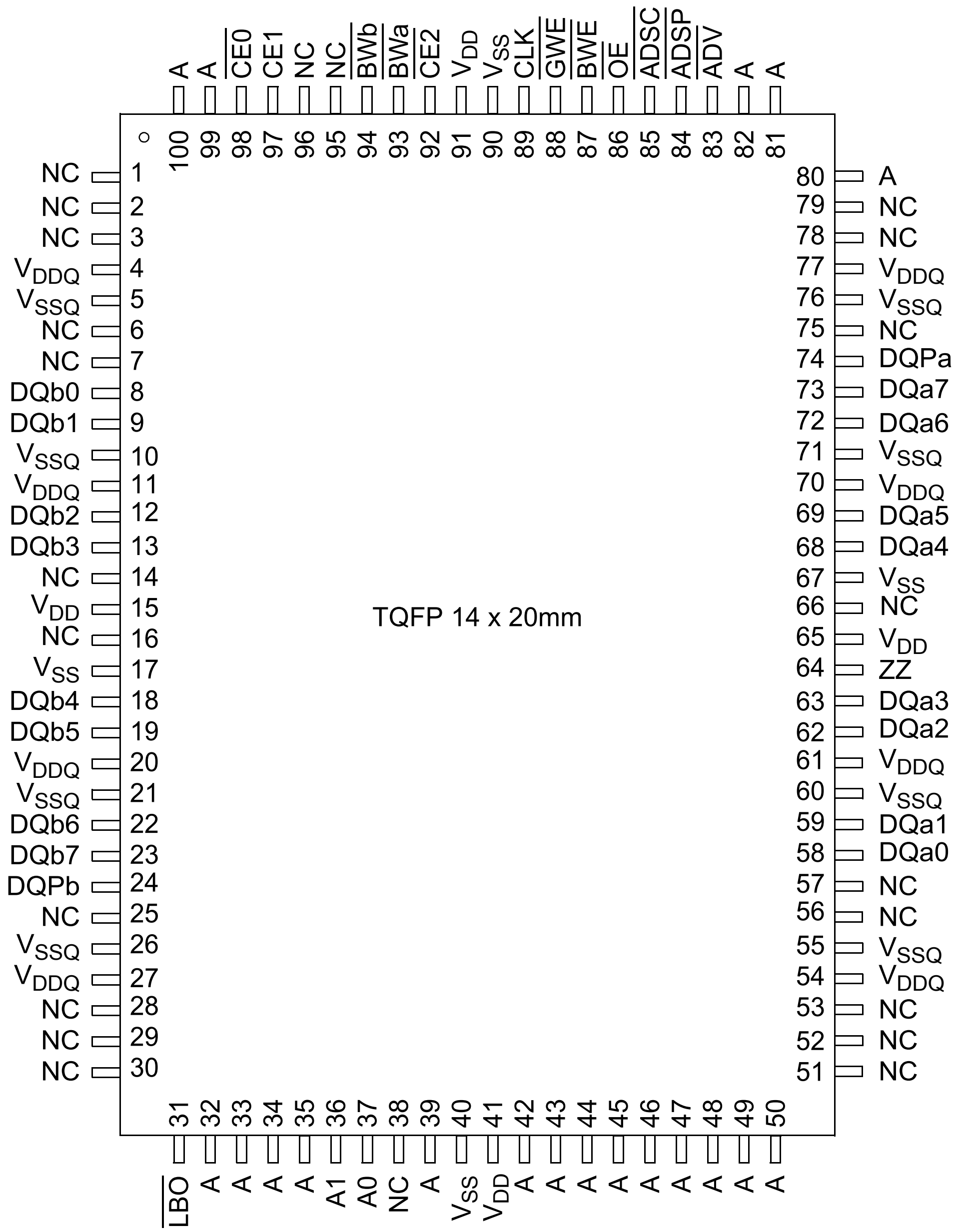
1 Core Power Supply: VDD = 3.3V ± 0.165V
2 I/O Supply Voltage: VDDQ = 3.3V ± 0.165V for 3.3V I/O
VDDQ = 2.5V ± 0.125V for 2.5V I/O

PL-SCD : Pipelined Burst Synchronous SRAM - Single Cycle Deselect
PL-DCD : Pipelined Burst Synchronous SRAM - Double Cycle Deselect
FT : Flow-through Burst Synchronous SRAM
NTD[1]-PL : Pipelined Burst Synchronous SRAM with NTD™
NTD-FT : Flow-through Burst Synchronous SRAM with NTD™

1NTD: No Turnaround Delay. NTD™ is a trademark of Alliance Semiconductor Corporation. All trademarks mentioned in this document are the property of their respective owners.

Pin assignment

100-pin TQFP - top view



Functional description

The AS7C332MFT18A is a high-performance CMOS 32-Mbit synchronous Static Random Access Memory (SRAM) device organized as 2,097152 words × 18 bits.

Fast cycle times of 8.5/10/12 ns with clock access times (t_{CD}) of 7.5/8.5/10 ns. Three chip enable (CE) inputs permit easy memory expansion. Burst operation is initiated in one of two ways: the controller address strobe (ADSC), or the processor address strobe (ADSP). The burst advance pin (ADV) allows subsequent internally generated burst addresses.

Read cycles are initiated with ADSP (regardless of WE and ADSC) using the new external address clocked into the on-chip address register when ADSP is sampled low, the chip enables are sampled active, and the output buffer is enabled with OE. In a read operation, the data accessed by the current address registered in the address registers by the positive edge of CLK are carried to the data-out buffer. ADV is ignored on the clock edge that samples ADSP asserted, but is sampled on all subsequent clock edges. Address is incremented internally for the next access of the burst when ADV is sampled low and both address strobes are high. Burst mode is selectable with the LBO input. With LBO unconnected or driven high, burst operations use an interleaved count sequence. With LBO driven low, the device uses a linear count sequence.

Write cycles are performed by disabling the output buffers with OE and asserting a write command. A global write enable GWE writes all 18 bits regardless of the state of individual BW[a,b] inputs. Alternately, when GWE is high, one or more bytes may be written by asserting BWE and the appropriate individual byte BWn signals.

BWn is ignored on the clock edge that samples ADSP low, but it is sampled on all subsequent clock edges. Output buffers are disabled when BWn is sampled LOW regardless of OE. Data is clocked into the data input register when BWn is sampled low. Address is incremented internally to the next burst address if BWn and ADV are sampled low.

Read or write cycles may also be initiated with ADSC instead of ADSP. The differences between cycles initiated with ADSC and ADSP follow.

- ADSP must be sampled high when ADSC is sampled low to initiate a cycle with ADSC.
- WE signals are sampled on the clock edge that samples ADSC low (and ADSP high).
- Master chip enable CE0 blocks ADSP, but not ADSC.

The AS7C332MFT18A family operates from a core 3.3V power supply. I/Os use a separate power supply that can operate at 2.5V or 3.3V. These devices are available in a 100-pin TQFP package.

TQFP capacitance

Parameter	Symbol	Test conditions	Min	Max	Unit
Input capacitance	C_{IN}*	$V_{IN} = 0V$	-	5	pF
I/O capacitance	$C_{I/O}$*	$V_{OUT} = 0V$	-	7	pF

*Guaranteed not tested

TQFP thermal resistance

Description	Conditions		Symbol	Typical	Units
Thermal resistance (junction to ambient)[1]	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/JESD51	1–layer	θ_{JA}	40	°C/W
		4–layer	θ_{JA}	22	°C/W
Thermal resistance (junction to top of case)[1]			θ_{JC}	8	°C/W

1 This parameter is sampled

Signal descriptions

Pin	I/O	Properties	Description
CLK	I	CLOCK	Clock. All inputs except $\overline{OE}$, ZZ, and $\overline{LBO}$ are synchronous to this clock.
A,A0,A1	I	SYNC	Address. Sampled when all chip enables are active and when $\overline{ADSC}$ or $\overline{ADSP}$ are asserted.
DQ[a,b]	I/O	SYNC	Data. Driven as output when the chip is enabled and when $\overline{OE}$ is active.
$\overline{CE0}$	I	SYNC	Master chip enable. Sampled on clock edges when $\overline{ADSP}$ or $\overline{ADSC}$ is active. When $\overline{CE0}$ is inactive, $\overline{ADSP}$ is blocked. Refer to the “Synchronous truth table” for more information.
CE1, $\overline{CE2}$	I	SYNC	Synchronous chip enables, active high, and active low, respectively. Sampled on clock edges when $\overline{ADSC}$ is active or when $\overline{CE0}$ and $\overline{ADSP}$ are active.
$\overline{ADSP}$	I	SYNC	Address strobe processor. Asserted low to load a new address or to enter standby mode.
$\overline{ADSC}$	I	SYNC	Address strobe controller. Asserted low to load a new address or to enter standby mode.
$\overline{ADV}$	I	SYNC	Advance. Asserted low to continue burst read/write.
$\overline{GWE}$	I	SYNC	Global write enable. Asserted low to write all 18 bits. When high, $\overline{BWE}$ and $\overline{BW[a,b]}$ control write enable.
$\overline{BWE}$	I	SYNC	Byte write enable. Asserted low with $\overline{GWE}$ high to enable effect of $\overline{BW[a,b]}$ inputs.
$\overline{BW[a,b]}$	I	SYNC	Write enables. Used to control write of individual bytes when $\overline{GWE}$ is high and $\overline{BWE}$ is low. If any of $\overline{BW[a,b]}$ is active with $\overline{GWE}$ high and $\overline{BWE}$ low, the cycle is a write cycle. If all $\overline{BW[a,b]}$ are inactive, the cycle is a read cycle.
$\overline{OE}$	I	ASYNC	Asynchronous output enable. I/O pins are driven when $\overline{OE}$ is active and chip is in read mode.
$\overline{LBO}$	I	STATIC	Selects Burst mode. When tied to V_{DD} or left floating, device follows interleaved Burst order. When driven Low, device follows linear Burst order. *This signal is internally pulled High.*
ZZ	I	ASYNC	Snooze. Places device in low power mode; data is retained. Connect to GND if unused.
NC	-	-	No connect

Snooze Mode

SNOOZE MODE is a low current, power-down mode in which the device is deselected and current is reduced to I_{SB2}. The duration of SNOOZE MODE is dictated by the length of time the ZZ is in a High state.

The ZZ pin is an asynchronous, active high input that causes the device to enter SNOOZE MODE.

When the ZZ pin becomes a logic High, I_{SB2} is guaranteed after the time t_{ZZI} is met. After entering SNOOZE MODE, all inputs except ZZ is disabled and all outputs go to High-Z. Any operation pending when entering SNOOZE MODE is not guaranteed to successfully complete. Therefore, SNOOZE MODE (READ or WRITE) must not be initiated until valid pending operations are completed. Similarly, when exiting SNOOZE MODE during t_{PUS}, only a DESELECT or READ cycle should be given while the SRAM is transitioning out of SNOOZE MODE.

Write enable truth table (per byte)

Function	$\overline{GWE}$	$\overline{BWE}$	$\overline{BWa}$	$\overline{BWb}$
Write All Bytes	L	X	X	X
	H	L	L	L
Write Byte a	H	L	L	H
Write Byte b	H	L	H	L
Read	H	H	X	X
	H	L	H	H

Key: X = don't care, L = low, H = high, n = a, b; $\overline{BWE}$, $\overline{BWn}$ = internal write signal.

Asynchronous Truth Table

Operation	ZZ	$\overline{OE}$	I/O Status
Snooze mode	H	X	High-Z
Read	L	L	Dout
	L	H	High-Z
Write	L	X	Din, High-Z
Deselected	L	X	High-Z

Notes:
1. X means "Don't Care"
2. ZZ pin is pulled down internally
3. For write cycles that follows read cycles, the output buffers must be disabled with $\overline{OE}$, otherwise data bus contention will occur.
4. Snooze mode means power down state of which stand-by current does not depend on cycle times
5. Deselected means power down state of which stand-by current depends on cycle times

Burst sequence table

Interleaved burst address ($\overline{LBO}$ = 1)					Linear burst address ($\overline{LBO}$ = 0)				
	A1 A0	A1 A0	A1 A0	A1 A0		A1 A0	A1 A0	A1 A0	A1 A0
1st Address	0 0	0 1	1 0	1 1	1st Address	0 0	0 1	1 0	1 1
2nd Address	0 1	0 0	1 1	1 0	2nd Address	0 1	1 0	1 1	0 0
3rd Address	1 0	1 1	0 0	0 1	3rd Address	1 0	1 1	0 0	0 1
4th Address	1 1	1 0	0 1	0 0	4th Address	1 1	1 0	0 1	1 0

Synchronous truth table[4]

CE0[1]	CE1	CE2	ADSP	ADSC	ADV	WRITE[2]	OE	Address accessed	CLK	Operation	DQ
H	X	X	X	L	X	X	X	NA	L to H	Deselect	Hi–Z
L	L	X	L	X	X	X	X	NA	L to H	Deselect	Hi–Z
L	L	X	H	L	X	X	X	NA	L to H	Deselect	Hi–Z
L	X	H	L	X	X	X	X	NA	L to H	Deselect	Hi–Z
L	X	H	H	L	X	X	X	NA	L to H	Deselect	Hi–Z
L	H	L	L	X	X	X	L	External	L to H	Begin read	Q
L	H	L	L	X	X	X	H	External	L to H	Begin read	Hi–Z
L	H	L	H	L	X	H	L	External	L to H	Begin read	Q
L	H	L	H	L	X	H	H	External	L to H	Begin read	Hi–Z
X	X	X	H	H	L	H	L	Next	L to H	Continue read	Q
X	X	X	H	H	L	H	H	Next	L to H	Continue read	Hi–Z
X	X	X	H	H	H	H	L	Current	L to H	Suspend read	Q
X	X	X	H	H	H	H	H	Current	L to H	Suspend read	Hi–Z
H	X	X	X	H	L	H	L	Next	L to H	Continue read	Q
H	X	X	X	H	L	H	H	Next	L to H	Continue read	Hi–Z
H	X	X	X	H	H	H	L	Current	L to H	Suspend read	Q
H	X	X	X	H	H	H	H	Current	L to H	Suspend read	Hi–Z
L	H	L	H	L	X	L	X	External	L to H	Begin write	D[3]
X	X	X	H	H	L	L	X	Next	L to H	Continue write	D
H	X	X	X	H	L	L	X	Next	L to H	Continue write	D
X	X	X	H	H	H	L	X	Current	L to H	Suspend write	D
H	X	X	X	H	H	L	X	Current	L to H	Suspend write	D

1 X = don't care, L = low, H = high
2 For WRITE, L means any one or more byte write enable signals (BWa or BWb) and BWE are LOW or GWE is LOW. WRITE = HIGH for all BWx, BWE, GWE HIGH. See "Write enable truth table (per byte)," on page 6 for more information.
3 For write operation following a READ, OE must be high before the input data set up time and held high throughout the input hold time
4 ZZ pin is always Low.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Power supply voltage relative to GND	V_{DD}, V_{DDQ}	–0.5	+4.6	V
Input voltage relative to GND (input pins)	V_{IN}	–0.5	V_{DD} + 0.5	V
Input voltage relative to GND (I/O pins)	V_{IN}	–0.5	V_{DDQ} + 0.5	V
Power dissipation	P_d	–	1.8	W
Short circuit output current	I_{OUT}	–	20	mA
Storage temperature	T_{stg}	–65	+150	^oC
Temperature under bias	T_{bias}	–65	+135	^oC

Stresses greater than those listed under "Absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions may affect reliability.

Recommended operating conditions at 3.3V I/O

Parameter	Symbol	Min	Nominal	Max	Unit
Supply voltage for inputs	V_{DD}	3.135	3.3	3.465	V
Supply voltage for I/O	V_{DDQ}	3.135	3.3	3.465	V
Ground supply	Vss	0	0	0	V

Recommended operating conditions at 2.5V I/O

Parameter	Symbol	Min	Nominal	Max	Unit
Supply voltage for inputs	V_{DD}	3.135	3.3	3.465	V
Supply voltage for I/O	V_{DDQ}	2.375	2.5	2.625	V
Ground supply	Vss	0	0	0	V

DC electrical characteristics for 3.3V I/O operation

Parameter	Sym	Conditions	Min	Max	Unit
Input leakage current†	$\|I_{LI}\|$	V_{DD} = Max, 0V ≤ V_{IN} ≤ V_{DD}	-2	2	µA
Output leakage current	$\|I_{LO}\|$	OE ≥ V_{IH}, V_{DD} = Max, 0V ≤ V_{OUT} ≤ V_{DDQ}	-2	2	µA
Input high (logic 1) voltage	V_{IH}	Address and control pins	2*	V_{DD}+0.3	V
		I/O pins	2*	V_{DDQ}+0.3	
Input low (logic 0) voltage	V_{IL}	Address and control pins	-0.3**	0.8	V
		I/O pins	-0.5**	0.8	
Output high voltage	V_{OH}	I_{OH} = –4 mA, V_{DDQ} = 3.135V	2.4	–	V
Output low voltage	V_{OL}	I_{OL} = 8 mA, V_{DDQ} = 3.465V	–	0.4	V

DC electrical characteristics for 2.5V I/O operation

Parameter	Sym	Conditions	Min	Max	Unit
Input leakage current†	$\|I_{LI}\|$	V_{DD} = Max, 0V ≤ V_{IN} ≤ V_{DD}	-2	2	µA
Output leakage current	$\|I_{LO}\|$	OE ≥ V_{IH}, V_{DD} = Max, 0V ≤ V_{OUT} ≤ V_{DDQ}	-2	2	µA
Input high (logic 1) voltage	V_{IH}	Address and control pins	1.7*	V_{DD}+0.3	V
		I/O pins	1.7*	V_{DDQ}+0.3	V
Input low (logic 0) voltage	V_{IL}	Address and control pins	-0.3**	0.7	V
		I/O pins	-0.3**	0.7	V
Output high voltage	V_{OH}	I_{OH} = –4 mA, V_{DDQ} = 2.375V	1.7	–	V
Output low voltage	V_{OL}	I_{OL} = 8 mA, V_{DDQ} = 2.625V	–	0.7	V

† $\overline{LBO}$ and ZZ pins have an internal pull-up or pull-down, and input leakage = ±10 µA.
*V_{IH} max < VDD +1.5V for pulse width less than 0.2 X t_{CYC}
**V_{IL} min = -1.5 for pulse width less than 0.2 X t_{CYC}

I_{DD} operating conditions and maximum limits

Parameter	Sym	Conditions	-75	-85	-10	Unit
Operating power supply current[1]	I_{CC}	$\overline{CE0}$ ≤ V_{IL}, CE1 ≥ V_{IH}, $\overline{CE2}$ ≤ V_{IL}, f = f_{Max}, I_{OUT} = 0 mA, ZZ ≤ V_{IL}	325	300	275	mA
Standby power supply current	I_{SB}	All V_{IN} ≤ 0.2V or ≥ V_{DD} – 0.2V, Deselected, f = f_{Max}, ZZ ≤ V_{IL}	140	130	130	mA
	I_{SB1}	Deselected, f = 0, ZZ ≤ 0.2V, all V_{IN} ≤ 0.2V or ≥ V_{DD} – 0.2V	90	90	90	
	I_{SB2}	Deselected, f = f_{Max}, ZZ ≥ V_{DD} – 0.2V, all V_{IN} ≤ V_{IL} or ≥ V_{IH}	80	80	80	

1 I_{CC} given with no output loading. I_{CC} increases with faster cycle times and greater output loading.

Timing characteristics over operating range

Parameter	Sym	–75		–85		–10		Unit	Notes[1]
		Min	Max	Min	Max	Min	Max		
Cycle time	t_{CYC}	8.5	–	10	–	12	–	ns	
Clock access time	t_{CD}	–	7.5	–	8.5	–	10	ns	
Output enable low to data valid	t_{OE}	–	3.5	–	4.0	–	4.0	ns	
Clock high to output low Z	t_{LZC}	2.5	–	2.5	–	2.5	–	ns	2,3,4
Data output invalid from clock high	t_{OH}	2.5	–	2.5	–	2.5	–	ns	2
Output enable low to output low Z	t_{LZOE}	0	–	0	–	0	–	ns	2,3,4
Output enable high to output high Z	t_{HZOE}	-	3.5	–	4.0	–	4.0	ns	2,3,4
Clock high to output high Z	t_{HZC}	-	4.0	–	5.0	–	5.0	ns	2,3,4
Output enable high to invalid output	t_{OHOE}	0	–	0	–	0	–	ns	
Clock high pulse width	t_{CH}	2.5	–	3.0	–	3.0	–	ns	5
Clock low pulse width	t_{CL}	2.5	–	3.0	–	3.0	–	ns	5
Address setup to clock high	t_{AS}	2.0	–	2.0	–	2.0	–	ns	6
Data setup to clock high	t_{DS}	2.0	–	2.0	–	2.0	–	ns	6
Write setup to clock high	t_{WS}	2.0	–	2.0	–	2.0	–	ns	6,7
Chip select setup to clock high	t_{CSS}	2.0	–	2.0	–	2.0	–	ns	6,8
Address hold from clock high	t_{AH}	0.5	–	0.5	–	0.5	–	ns	6
Data hold from clock high	t_{DH}	0.5	–	0.5	–	0.5	–	ns	6
Write hold from clock high	t_{WH}	0.5	–	0.5	–	0.5	–	ns	6,7
Chip select hold from clock high	t_{CSH}	0.5	–	0.5	–	0.5	–	ns	6,8
$\overline{ADV}$ setup to clock high	t_{ADVS}	2.0	–	2.0	–	2.0	–	ns	6
$\overline{ADSP}$ setup to clock high	t_{ADSPS}	2.0	–	2.0	–	2.0	–	ns	6
$\overline{ADSC}$ setup to clock high	t_{ADSCS}	2.0	–	2.0	–	2.0	–	ns	6
$\overline{ADV}$ hold from clock high	t_{ADVH}	0.5	–	0.5	–	0.5	–	ns	6
$\overline{ADSP}$ hold from clock high	t_{ADSPH}	0.5	–	0.5	–	0.5	–	ns	6
$\overline{ADSC}$ hold from clock high	t_{ADSCH}	0.5	–	0.5	–	0.5	–	ns	6

1 See “Notes” on page 16.

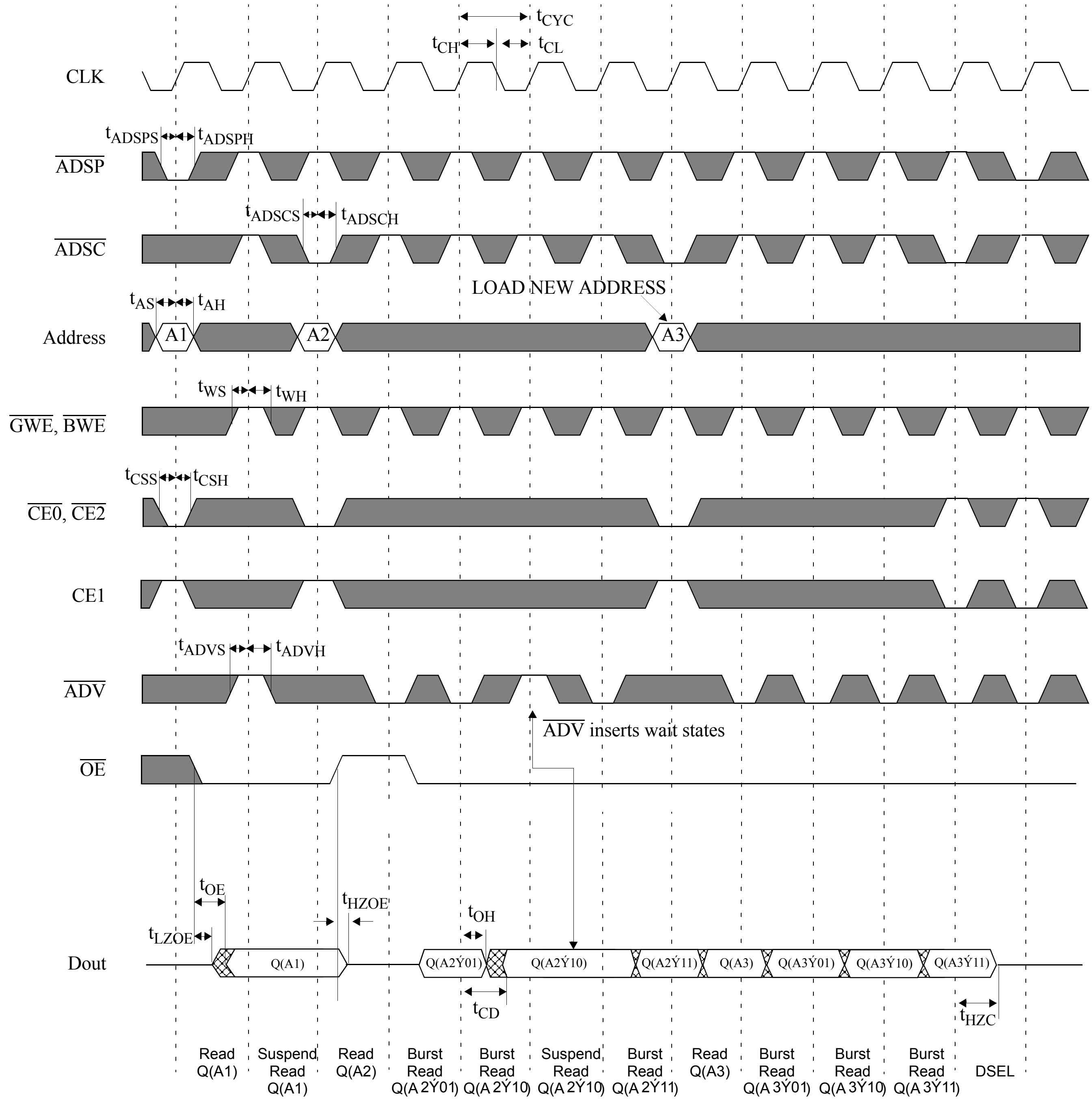
Snooze Mode Electrical Characteristics

Description	Conditions	Symbol	Min	Max	Units
Current during Snooze Mode	$ZZ \geq V_{IH}$	I_{SB2}		80	mA
ZZ active to input ignored		t_{PDS}	2		cycle
ZZ inactive to input sampled		t_{PUS}	2		cycle
ZZ active to SNOOZE current		t_{ZZI}		2	cycle
ZZ inactive to exit SNOOZE current		t_{RZZI}	0		

Key to switching waveforms

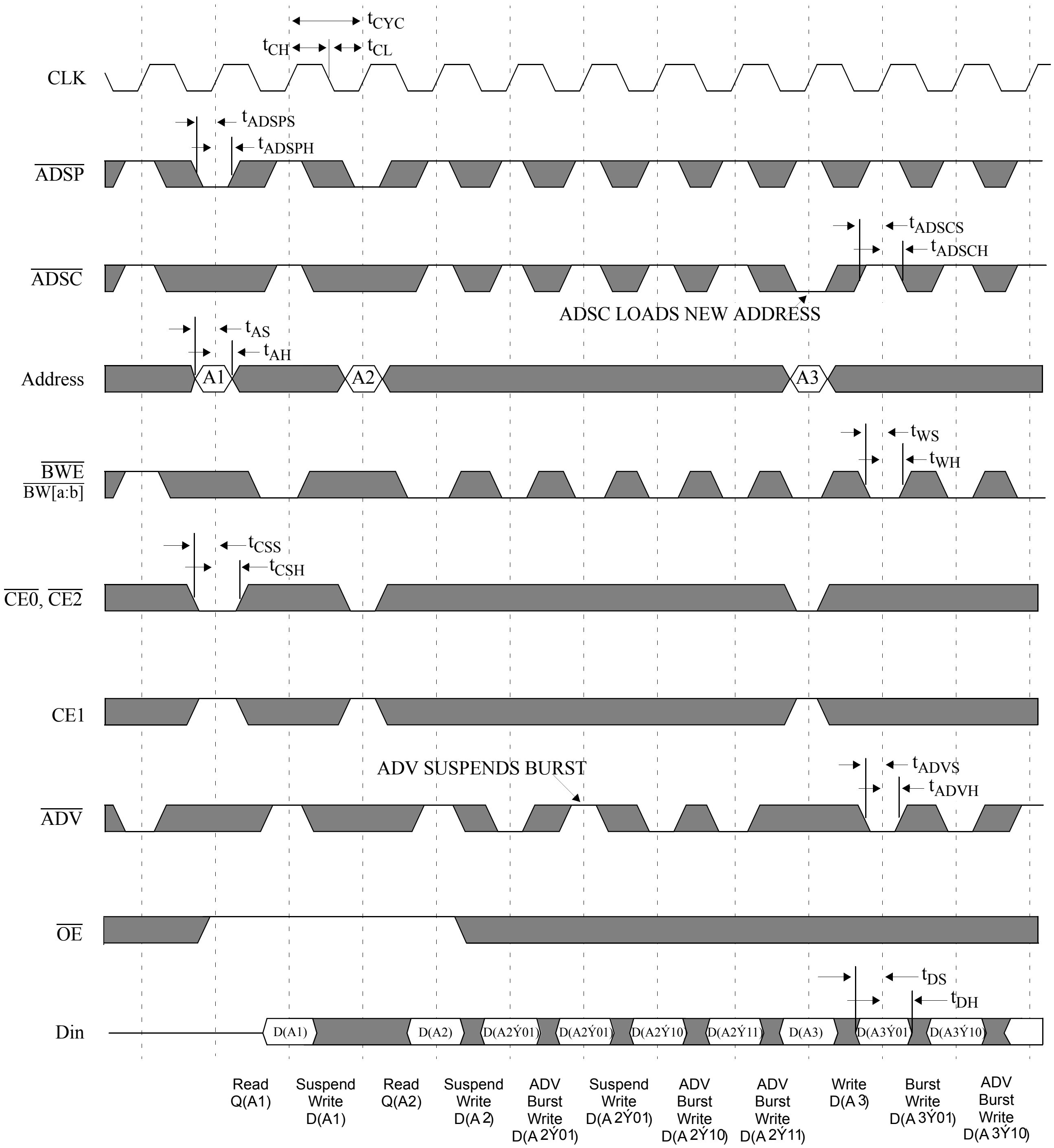
Rising input   Falling input   don't care   Undefined

Timing waveform of read cycle



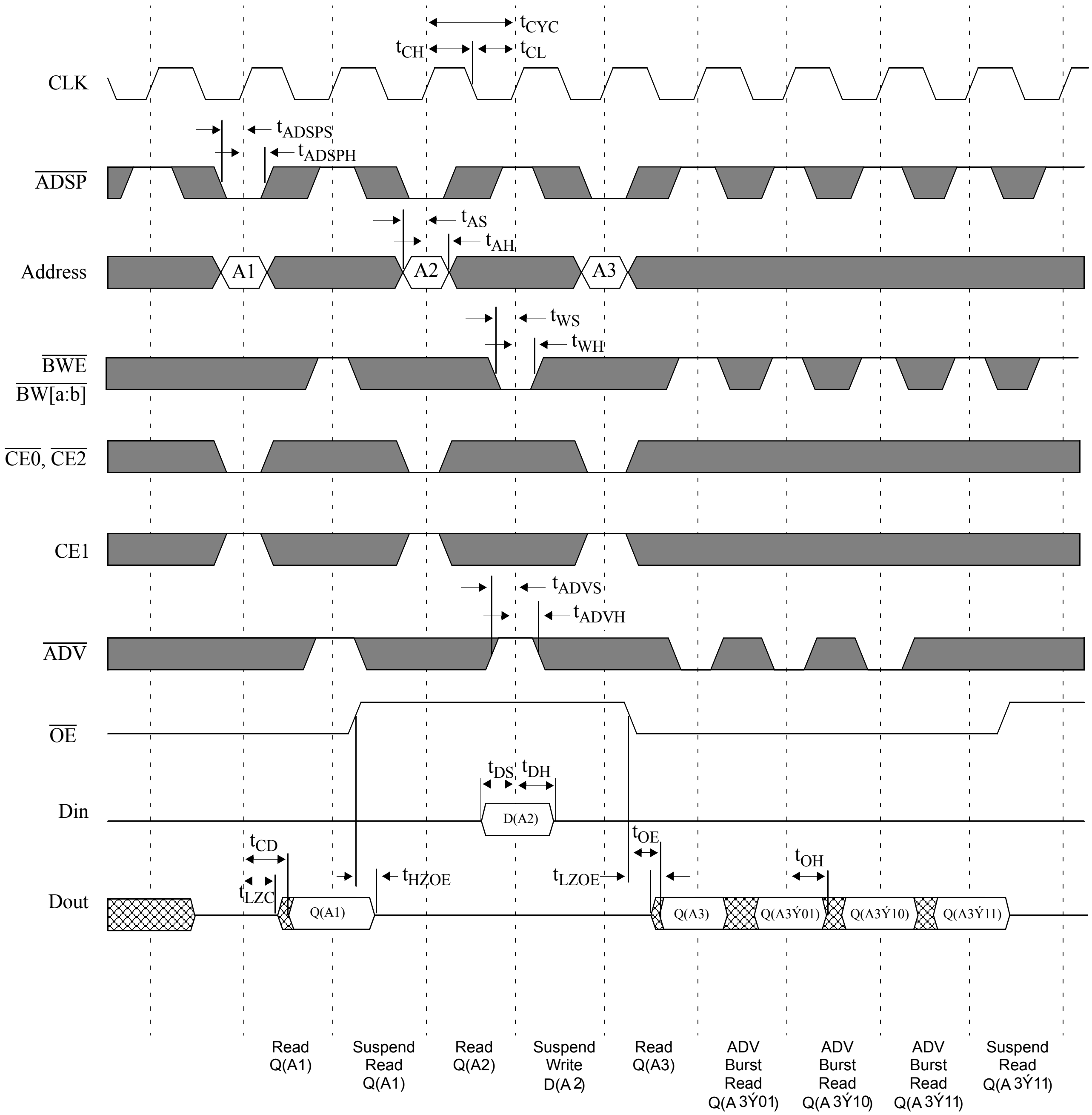
Note: Ý = XOR when LBO = high/no connect; Ý = ADD when LBO = low. BW[a:b] is don't care.

Timing waveform of write cycle



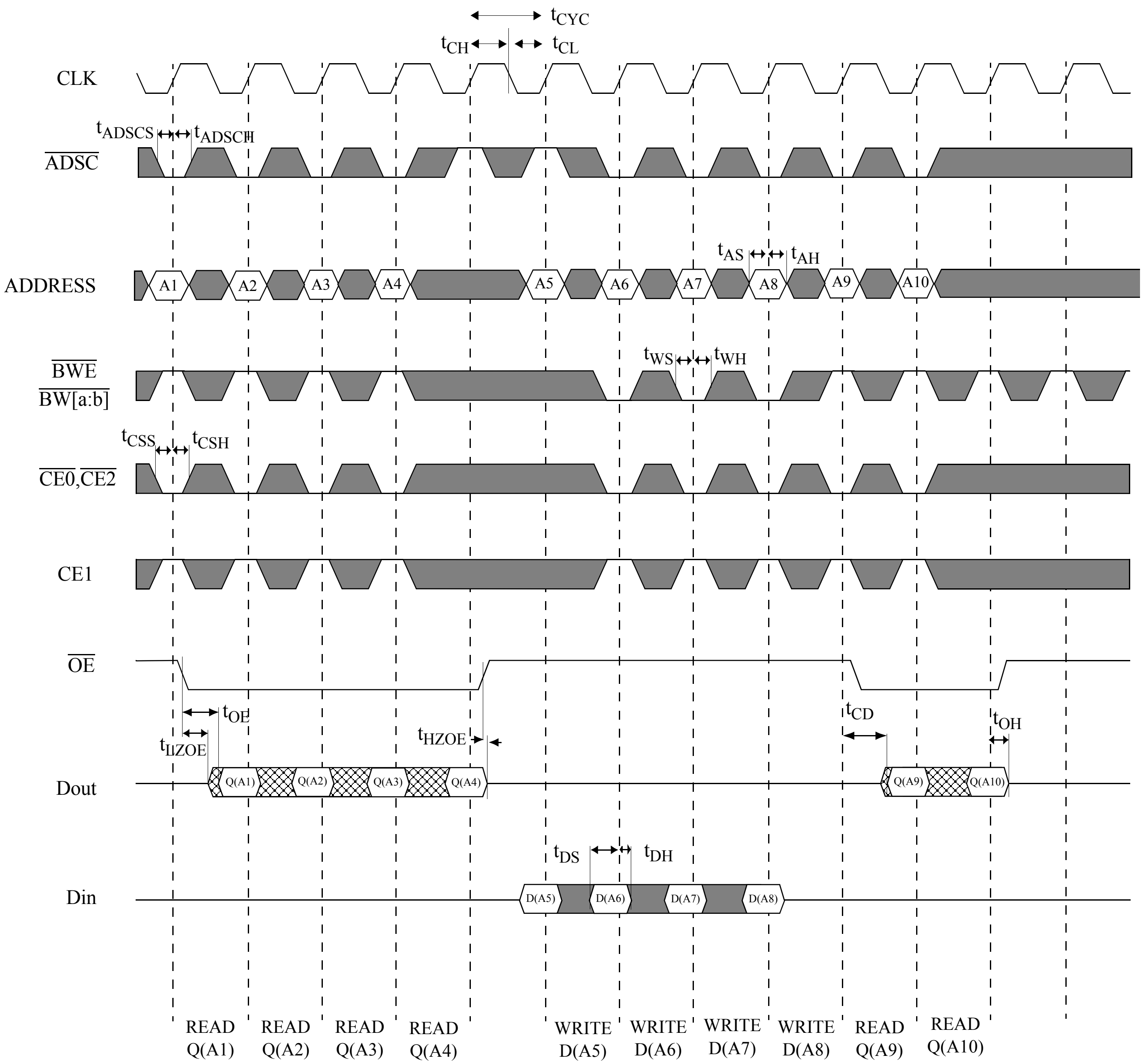
Note: Ý = XOR when $\overline{LBO}$ = high/no connect; Ý = ADD when $\overline{LBO}$ = low.

Timing waveform of read/write cycle ($\overline{\text{ADSP}}$ Controlled; $\overline{\text{ADSC}}$ High)



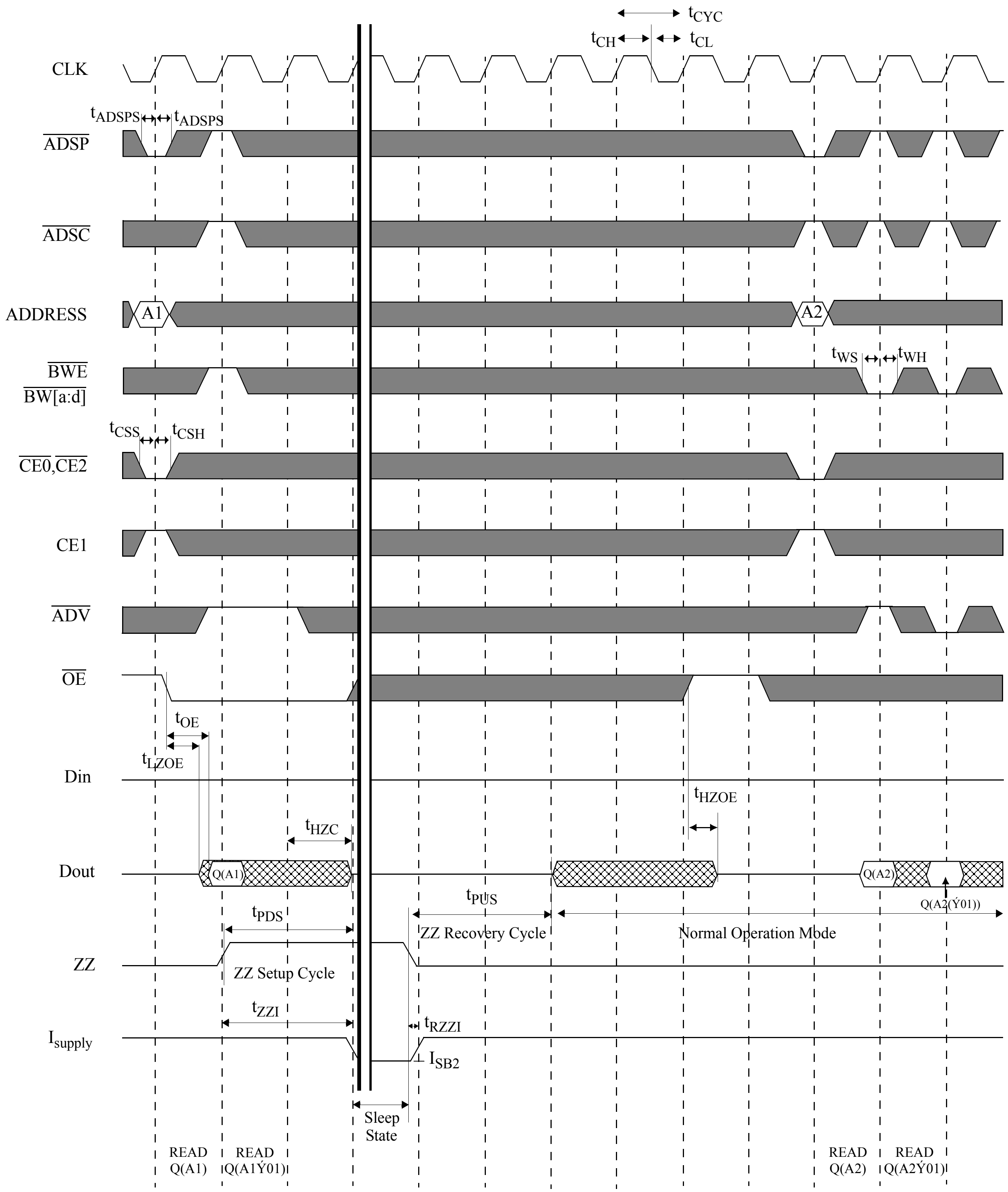
Note: Ý = XOR when $\overline{\text{LBO}}$ = high/no connect; Ý = ADD when $\overline{\text{LBO}}$ = low.

Timing waveform of read/write cycle($\overline{ADSC}$ controlled, $\overline{ADSP}$ = HIGH)



Note: $\overline{ADV}$ is don't care here.

Timing waveform of power down cycle



AC test conditions

- Output load: For t_{LZC}, t_{LZOE}, t_{HZOE}, t_{HZC}, see Figure C. For all others, see Figure B.
- Input pulse level: GND to 3V. See Figure A.
- Input rise and fall time (measured at 0.3V and 2.7V): 2 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

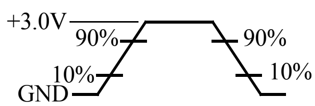


Figure A: Input waveform

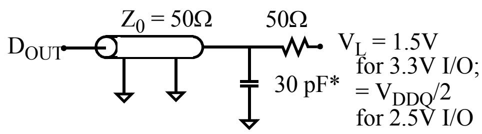


Figure B: Output load (A)

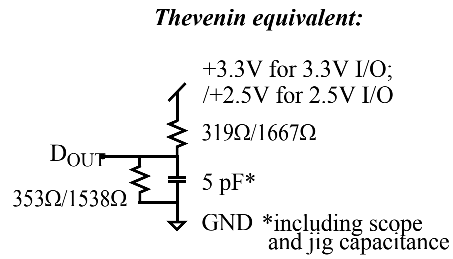


Figure C: Output load(B)

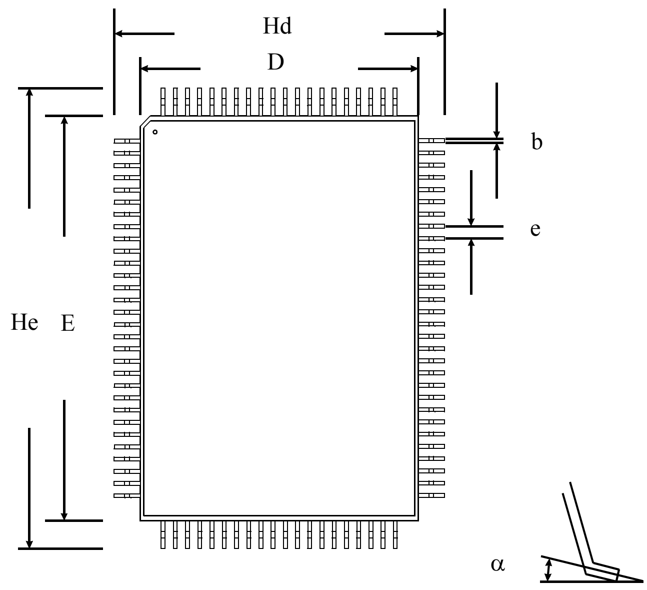
Notes

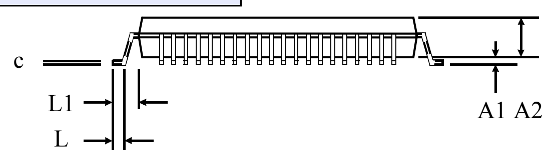
1 For test conditions, see "AC test conditions", Figures A, B, and C.
2 This parameter is measured with output load condition in Figure C.
3 This parameter is sampled but not 100% tested.
4 t_{HZOE} is less than t_{LZOE}, and t_{HZC} is less than t_{LZC} at any given temperature and voltage.
5 t_{CH} is measured as high if above VIH, and t_{CL} is measured as low if below VIL.
6 This is a synchronous device. All addresses must meet the specified setup and hold times for all rising edges of CLK. All other synchronous inputs must meet the setup and hold times for all rising edges of CLK when chip is enabled.
7 Write refers to $\overline{GWE}$, $\overline{BWE}$, and $\overline{BW[a,b]}$.
8 Chip select refers to $\overline{CE0}$, CE1, and $\overline{CE2}$.

Package dimensions

100-pin quad flat pack (TQFP)

	TQFP	
	Min	Max
A1	0.05	0.15
A2	1.35	1.45
b	0.22	0.38
c	0.09	0.20
D	13.90	14.10
E	19.90	20.10
e	0.65 nominal	
Hd	15.85	16.15
He	21.80	22.20
L	0.45	0.75
L1	1.00 nominal	
α	0°	7°
Dimensions in millimeters		





Ordering information

Package & Width	-75	-85	-10
TQFP x 18	AS7C332MFT18A-75TQC	AS7C332MFT18A-85TQC	AS7C332MFT18A-10TQC
	AS7C332MFT18A-75TQI	AS7C332MFT18A-85TQI	AS7C332MFT18A-10TQI

Note: Add suffix 'N' to the above part number for Lead Free Parts (Ex. AS7C332MFT18A-75TQCN)

Part numbering guide

AS7C	33	2M	FT	18	A	–XX	TQ	C/I	X
1	2	3	4	5	6	7	8	9	10

1.Alliance Semiconductor SRAM prefix

2.Operating voltage: 33 = 3.3V

3.Organization: 2M = 2Meg

4.Flow-through mode

5.Organization: 18 = x 18

6.Production version: A = first production version

7.Clock access time: [-75 = 7.5 ns;-85 = 8.5 ns; -10 = 10.0 ns]

8.Package type: TQ = TQFP

9.Operating temperature: C = commercial (0° C to 70° C); I = industrial (-40° C to 85° C)

10. N = Lead free part

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Part Number: AS7C332MFT18A
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